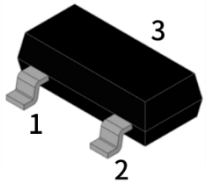
SS8550LST1

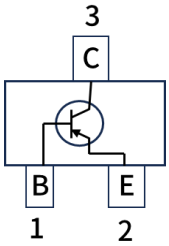
General Purpose Transistors PNP

1. FEATURES

- The material of product compliance with RoHS requirements and Halogen Free.
- High Stability and High Reliability.
- Complementary to SS8050LST1(NPN)
- High current capacity in compact package. IC =1.5 A.



SOT23 (TO-236)



2. Mechanical Data

- SOT-23 Small Outline Plastic Package.
- Tin plated leads, solderable per J-STD-002 and JESD22-B102.
- Marking: Y2

3. ORDERING INFORMATION

Device	Min Pack	Inner Box	Outer Carton	Reel
SS8550LST1	3000	45000	180000	7 inch

4. MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Limit	Unit
Collector-Emitter Voltage	VCEO	-25	V
Collector-Base Voltage	VCBO	-40	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current--Continuous	Ic	-1500	mA
Collector Power Dissipation	Pc	300	mW

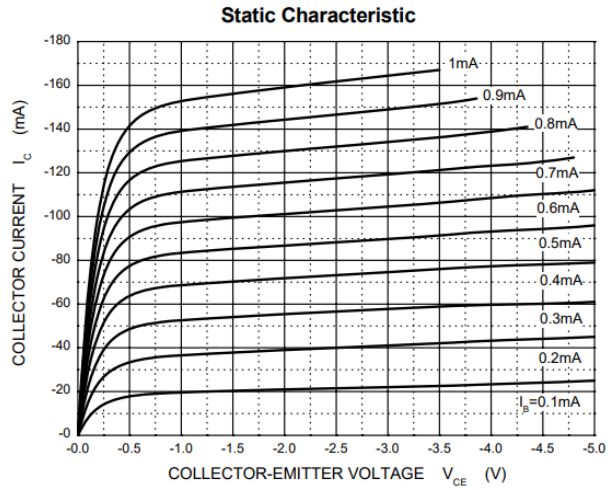
5. THERMAL CHARACTERISTICS

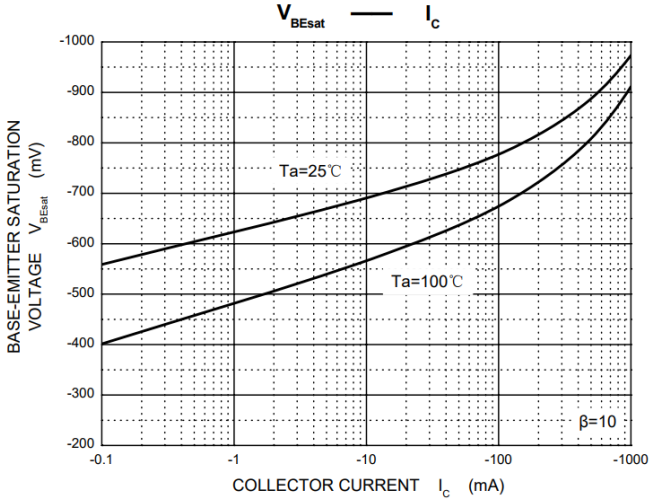
Parameter	Symbol	Limit	Unit
Operation Junction and Storage Temperature Range	TSTG	-55~150	°C
Thermal Resistance Junction to Ambient	RΘJA	417	°C/W

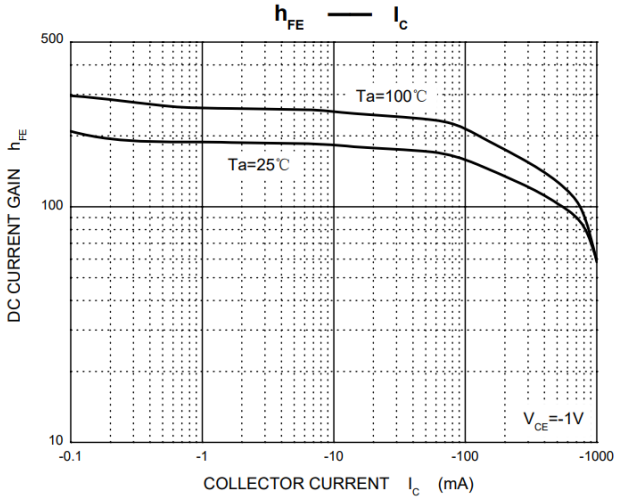
6. ELECTRICAL CHARACTERISTICS (Ta= 25°C unless otherwise specified)

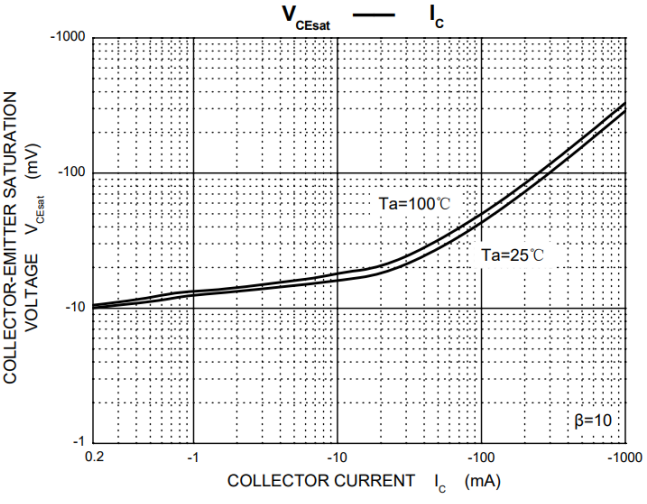
Parameter	Symbol	Condition	Min	Max	Unit
Collector–Emitter Breakdown Voltage	V(BR)CEO	IC = -0.1mA, IB = 0	-25		V
Collector–Base Breakdown Voltage	V(BR)CBO	IC = -100 μA, IE = 0	-40		V
Emitter–Base Breakdown Voltage	V(BR)EBO	IE = -100 μA, IC = 0	-5		V
Collector Cutoff current	ICEO	VCE = -20 V, IB = 0		-100	nA
Collector Cutoff Current	ICBO	VCB= -40 V, IE=0		-100	nA
Emitter cut-off current	IEBO	VEB= -5V, IC=0		-100	nA
DC current gain	hFE(1)	VCE=-1V, IC=-5mA	60		
DC current gain	hFE(2)	VCE=-1V, IC=-100mA	120	350	
DC current gain	hFE(3)	VCE=-1V, IC=-800mA	50		
Collector-Emitter Saturation voltage	VCE(sat)	IC=-800mA, IB=-80mA		-0.6	V
Base–Emitter Saturation Voltage	VBE(sat)	C=-800mA, IB=-80mA		-1.2	V
Transition frequency	fT	VCE=-10V, IC=-50mA, f=30MHz	100		MHz
Collector output capacitance	Cob	VCB=-10V, IE=0, f=1MHz		20	pF

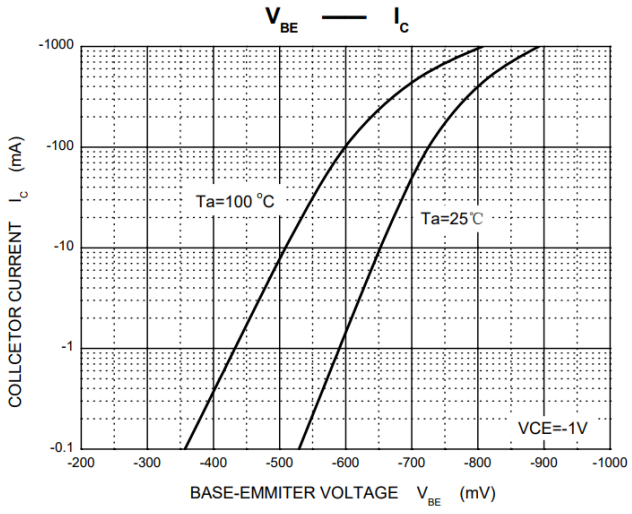
7. ELECTRICAL CHARACTERISTICS CURVES

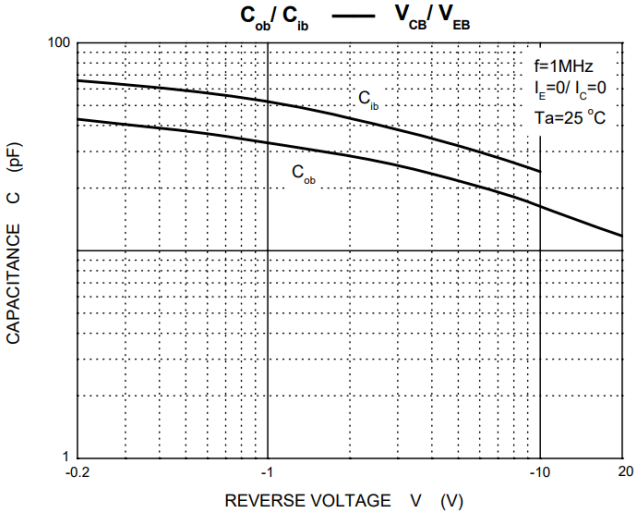




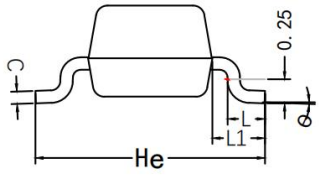


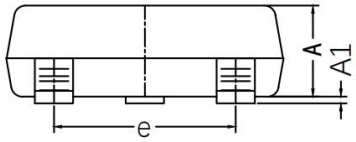


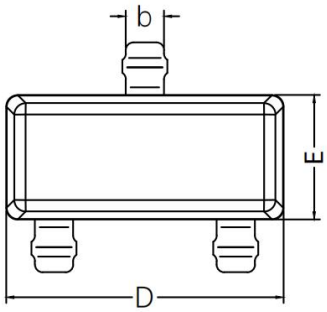




8. OUTLINE AND DIMENSIONS

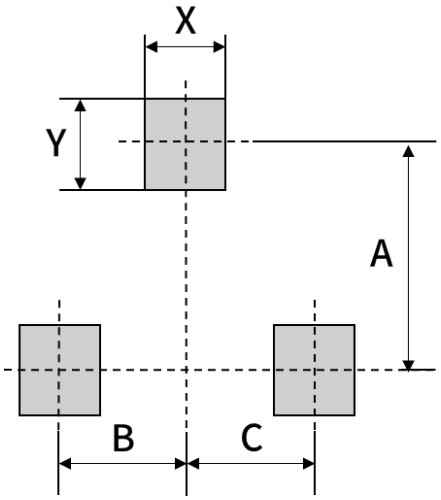






DIM	MIN	NOR	MAX
A	0.85	0.95	1.05
A1	0.01	0.06	0.10
b	0.36	0.44	0.52
c	0.09	0.13	0.18
D	2.80	2.90	3.10
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.40	0.50
L1	0.35	0.50	0.65
He	2.10	2.35	2.50
θ	0°	-	10°
All Dimensions in mm			

9. SUGGESTED PAD LAYOUT



SOT23		
DIM	mm	inch
A	2.00	0.079
B	0.95	0.037
C	0.95	0.037
X	0.80	0.031
Y	0.90	0.035

10. DISCLAIMER

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